

# Jaroslav Z Domagala

## List of Publications by Citations

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241  
papers

2,267  
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24  
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259  
ext. papers

2,487  
ext. citations

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avg, IF

4.24  
L-index

#	Paper	IF	Citations
241	Antioxidant activity of some phenolic constituents from green pepper ( <i>Piper nigrum</i> L.) and fresh nutmeg mace ( <i>Myristica fragrans</i> ). <i>Food Chemistry</i> , <b>2007</b> , 101, 515-523	8.5	90
240	Structural and magnetic properties of GaMnAs layers with high Mn-content grown by migration-enhanced epitaxy on GaAs(100) substrates. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 3271-3273	3.4	56
239	Influence of defects on the lattice constant of GaMnAs. <i>Physical Review B</i> , <b>2004</b> , 69,	3.3	55
238	Observation of topological crystalline insulator surface states on (111)-oriented Pb <sub>1-x</sub> SnxSe films. <i>Physical Review B</i> , <b>2014</b> , 89,	3.3	53
237	Structural and magnetic properties of molecular beam epitaxy grown GaMnAs layers. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2000</b> , 18, 1697		52
236	Basic ammonothermal growth of Gallium Nitride   State of the art, challenges, perspectives. <i>Progress in Crystal Growth and Characterization of Materials</i> , <b>2018</b> , 64, 63-74	3.5	51
235	Postgrowth annealing of (Ga,Mn) As under As capping: An alternative way to increase TC. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 112501	3.4	49
234	The microstructure of gallium nitride monocrystals grown at high pressure. <i>Journal of Crystal Growth</i> , <b>1996</b> , 169, 235-242	1.6	47
233	The influence of lattice parameter variation on microstructure of GaN single crystals. <i>Journal of Alloys and Compounds</i> , <b>2005</b> , 401, 261-264	5.7	34
232	Monocrystalline zinc oxide films grown by atomic layer deposition. <i>Thin Solid Films</i> , <b>2010</b> , 518, 4556-4559	2.2	33
231	Misfit strain anisotropy in partially relaxed lattice-mismatched InGaAs/GaAs heterostructures. <i>Journal of Physics Condensed Matter</i> , <b>2004</b> , 16, S1-S8	1.8	33
230	Effect of Mn interstitials on the lattice parameter of Ga <sub>1-x</sub> MnxAs. <i>Journal of Applied Physics</i> , <b>2004</b> , 95, 603-608	2.5	33
229	Structural properties of 10 <sup>4</sup> Å thick InN grown on sapphire (0001). <i>Superlattices and Microstructures</i> , <b>2006</b> , 40, 246-252	2.8	32
228	Relaxation of InGaN thin layers observed by X-ray and transmission electron microscopy studies. <i>Journal of Electronic Materials</i> , <b>2001</b> , 30, 439-444	1.9	32
227	Lattice Constant of Doped Semiconductor. <i>Acta Physica Polonica A</i> , <b>1995</b> , 88, 837-840	0.6	32
226	Thermal properties of CaNdAlO <sub>4</sub> and SrLaAlO <sub>4</sub> single crystals. <i>Materials Research Bulletin</i> , <b>1992</b> , 27, 483-490	1.0	31
225	High-pressure high-temperature annealing of ion-implanted GaN films monitored by visible and ultraviolet micro-Raman scattering. <i>Journal of Applied Physics</i> , <b>2000</b> , 87, 2736-2741	2.5	30

224	Lattice dilation by free electrons in heavily doped GaAs:Si. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 539-541	3.4	30
223	Influence of GaN substrate off-cut on properties of InGaN and AlGaN layers. <i>Crystal Research and Technology</i> , <b>2012</b> , 47, 321-328	1.3	28
222	Monocrystalline ZnO Films on GaN/Al <sub>2</sub> O <sub>3</sub> by Atomic Layer Epitaxy in Gas Flow. <i>Chemistry of Materials</i> , <b>2004</b> , 16, 1447-1450	9.6	27
221	Thermal expansion of bulk and homoepitaxial GaN. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 1434-1436	3.4	27
220	Lattice parameter, microhardness and energy gap of bulk Zn <sub>1-x</sub> Be <sub>x</sub> Se alloys. <i>Solid State Communications</i> , <b>1998</b> , 107, 735-740	1.6	25
219	Growth of thin AlInN/GaN quantum wells for applications to high-speed intersubband devices at telecommunication wavelengths. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2006</b> , 24, 1505		24
218	MBE Growth and Properties of ZnTe- and CdTe-Based Nanowires. <i>Journal of the Korean Physical Society</i> , <b>2008</b> , 53, 3055-3063	0.6	24
217	Influence of milk protein cross-linking by transglutaminase on the rennet coagulation time and the gel properties. <i>Journal of the Science of Food and Agriculture</i> , <b>2016</b> , 96, 3500-7	4.3	23
216	Formation process and superparamagnetic properties of (Mn,Ga)As nanocrystals in GaAs fabricated by annealing of (Ga,Mn)As layers with low Mn content. <i>Physical Review B</i> , <b>2011</b> , 84,	3.3	22
215	Ferromagnetic GaMnAs/GaAs superlattices MBE growth and magnetic properties. <i>Thin Solid Films</i> , <b>2002</b> , 412, 122-128	2.2	22
214	Lateral Control of Indium Content and Wavelength of III-Nitride Diode Lasers by Means of GaN Substrate Patterning. <i>Applied Physics Express</i> , <b>2012</b> , 5, 021001	2.4	21
213	Correlation of optical and structural properties of GaN/AlN multi-quantum wells Ab initio and experimental study. <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 015703	2.5	21
212	Microscopic bending of GaAs layers grown by epitaxial lateral overgrowth. <i>Journal of Applied Physics</i> , <b>1998</b> , 84, 6937-6939	2.5	20
211	Lattice parameters of GaN single crystals, homoepitaxial layers and heteroepitaxial layers on sapphire. <i>Journal of Alloys and Compounds</i> , <b>1999</b> , 286, 271-275	5.7	20
210	Thermal strain in GaAs layers grown by epitaxial lateral overgrowth on Si substrates. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 2749-2751	3.4	19
209	Photoreflectance study of the fundamental optical properties of (Ga,Mn)As epitaxial films. <i>Physical Review B</i> , <b>2011</b> , 83,	3.3	18
208	Strain in GaAs layers grown by liquid phase epitaxial lateral overgrowth. <i>Journal of Applied Physics</i> , <b>1999</b> , 86, 1965-1969	2.5	18
207	Parameters of substrates Single crystals of ZnTe and Cd <sub>1-x</sub> Zn <sub>x</sub> Te (x. <i>Journal of Crystal Growth</i> , <b>1999</b> , 197, 423-426	1.6	18

206	ZnO by ALD - Advantages of the Material Grown at Low Temperature. <i>Acta Physica Polonica A</i> , <b>2009</b> , 116, 814-817	0.6	18
205	Hydrogen Sensing Properties of Thin NiO Films Deposited by RF Sputtering. <i>Procedia Engineering</i> , <b>2012</b> , 47, 746-749		17
204	Growth by atomic layer epitaxy and characterization of thin films of ZnO. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2005</b> , 2, 1125-1130		17
203	Influence of edge-grown HVPE GaN on the structural quality of c-plane oriented HVPE-GaN grown on ammonothermal GaN substrates. <i>Journal of Crystal Growth</i> , <b>2016</b> , 456, 80-85	1.6	16
202	Zinc oxide grown by atomic layer deposition is a material for novel 3D electronics. <i>Physica Status Solidi (B): Basic Research</i> , <b>2010</b> , 247, 1611-1615	1.3	15
201	Self-organized MnAs quantum dots formed during annealing of GaMnAs under arsenic capping. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 263114	3.4	15
200	Control of adhesion to the mask of epitaxial laterally overgrown GaAs layers. <i>Journal of Applied Physics</i> , <b>2001</b> , 90, 6140-6144	2.5	15
199	Synchrotron x-ray topographic and high-resolution diffraction analysis of mask-induced strain in epitaxial laterally overgrown GaAs layers. <i>Journal of Applied Physics</i> , <b>1999</b> , 86, 4298-4303	2.5	15
198	Band structure evolution and the origin of magnetism in (Ga,Mn)As: From paramagnetic through superparamagnetic to ferromagnetic phase. <i>Physical Review B</i> , <b>2018</b> , 97,	3.3	14
197	Experimental evidence for topological surface states wrapping around a bulk SnTe crystal. <i>Physical Review B</i> , <b>2017</b> , 96,	3.3	14
196	Structural properties of MBE grown GaMnAs layers. <i>Thin Solid Films</i> , <b>2000</b> , 367, 165-167	2.2	14
195	High power nitride laser diodes grown by plasma assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2015</b> , 425, 398-400	1.6	13
194	Impact of substrate temperature on magnetic properties of plasma-assisted molecular beam epitaxy grown (Ga,Mn)N. <i>Journal of Alloys and Compounds</i> , <b>2018</b> , 747, 946-959	5.7	13
193	Structural perfection of InGaN layers and its relation to photoluminescence. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2009</b> , 6, 2626-2631		13
192	Voids and Mn-rich inclusions in a (Ga,Mn)As ferromagnetic semiconductor investigated by transmission electron microscopy. <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 083546	2.5	13
191	Structural defects and compositional uniformity in CdTe and Cd <sub>1-x</sub> Zn <sub>x</sub> Te crystals grown by a vapour transport technique. <i>Journal of Crystal Growth</i> , <b>1998</b> , 191, 673-678	1.6	13
190	Modification of the local atomic structure around Mn atoms in (Ga, Mn)As layers by high temperature annealing. <i>Journal of Physics Condensed Matter</i> , <b>2007</b> , 19, 496205	1.8	13
189	Imaging of strain in laterally overgrown GaAs layers by spatially resolved x-ray diffraction. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 241904	3.4	13

188	Resistive and structural properties of La <sub>1.85</sub> Sr <sub>0.15</sub> Cu <sub>1-x</sub> Zn <sub>x</sub> O <sub>4</sub> films. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 2823-2825	3.4	13
187	Direct measurement of the lattice parameter of thick stable zinc-blende MgTe layer. <i>Journal of Alloys and Compounds</i> , <b>1999</b> , 286, 276-278	5.7	13
186	Temperature study of lattice constants and Raman scattering of SrLaGaO <sub>4</sub> single crystal. <i>Solid State Communications</i> , <b>1995</b> , 96, 785-788	1.6	13
185	Zinc-blende MnTe(111) on BaF <sub>2</sub> (111) substrates for optical measurements. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 3796-3798	3.4	13
184	Optical properties of pure and Ce <sup>3+</sup> doped gadolinium gallium garnet crystals and epitaxial layers. <i>Journal of Luminescence</i> , <b>2015</b> , 164, 31-37	3.8	12
183	Crystal Growth and Glass-Like Thermal Conductivity of Ca <sub>3</sub> RE <sub>2</sub> (BO <sub>3</sub> ) <sub>4</sub> (RE = Y, Gd, Nd) Single Crystals. <i>Crystals</i> , <b>2017</b> , 7, 88	2.3	12
182	. <i>IEEE Transactions on Nuclear Science</i> , <b>2011</b> , 58, 347-353	1.7	12
181	Comparison of dimethylzinc and diethylzinc as precursors for monocrystalline zinc oxide grown by atomic layer deposition method. <i>Physica Status Solidi (B): Basic Research</i> , <b>2010</b> , 247, 1699-1701	1.3	12
180	Spontaneous stratification of InGaN layers and its influence on optical properties. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2009</b> , 6, S433-S436		11
179	A channeling investigation of the structural modifications in uranium dioxide submitted to swift-ion irradiation and aqueous corrosion. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>1998</b> , 136-138, 465-470	1.2	11
178	Hybrid reciprocal space for X-ray diffraction in epitaxial layers. <i>Journal of Applied Crystallography</i> , <b>2007</b> , 40, 546-551	3.8	11
177	Tilt and dislocations in epitaxial laterally overgrown GaAs layers. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 013508	2.5	11
176	Mn enriched surface of annealed (GaMn)As layers annealed under arsenic capping. <i>Physical Review B</i> , <b>2007</b> , 75,	3.3	11
175	MBE Growth and Properties of GaMnAs(100) Films. <i>Acta Physica Polonica A</i> , <b>1998</b> , 94, 509-513	0.6	11
174	Hybrid reciprocal lattice: application to layer stress determination in GaAlN/GaN(0001) systems with patterned substrates. <i>Journal of Applied Crystallography</i> , <b>2016</b> , 49, 798-805	3.8	10
173	Triclinic deformation of InGaN layers grown on vicinal surface of GaN (00.1) substrates. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 113512	2.5	10
172	Structure Deformation in GdCOB Single Crystals Grown by the Czochralski Method. <i>Crystal Growth and Design</i> , <b>2008</b> , 8, 3253-3256	3.5	10
171	Monocrystalline thin films of ZnSe and ZnO grown by atomic layer epitaxy. <i>Vacuum</i> , <b>2004</b> , 74, 269-272	3.7	10

170	n-ZnO/p-4H-SiC diode: Structural, electrical, and photoresponse characteristics. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 101105	3.4	9
169	Rocksalt ZnMgO alloys for ultraviolet applications: Origin of band-gap fluctuations and direct-indirect transitions. <i>Physical Review B</i> , <b>2020</b> , 101,	3.3	9
168	Cubic anisotropy in (Ga,Mn)As layers: Experiment and theory. <i>Physical Review B</i> , <b>2018</b> , 97,	3.3	9
167	Tilt of InGaN layers on miscut GaN substrates. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2010</b> , 4, 142-144	3.4	9
166	Crystal Defects and Strain of Epitaxial InP Layers Laterally Overgrown on Si. <i>Crystal Growth and Design</i> , <b>2006</b> , 6, 1096-1100	3.5	9
165	Strain release in InGaAs/InxAl1-xAs/InP heterostructures. <i>Physica B: Condensed Matter</i> , <b>2003</b> , 340-342, 1082-1085	2.8	9
164	Depth-influenced structure through permeating polymer membrane using SAXS synchrotron method. <i>Journal of Membrane Science</i> , <b>2001</b> , 186, 1-8	9.6	9
163	Dependence of photoluminescence of silicon on conditions of pressure-annealing. <i>Journal of Alloys and Compounds</i> , <b>1999</b> , 286, 258-264	5.7	9
162	Experimental search for the origin of low-energy modes in topological materials. <i>Physical Review B</i> , <b>2019</b> , 100,	3.3	8
161	Effect of low-temperature annealing on the electronic- and band-structures of (Ga,Mn)As epitaxial layers. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 012009	2.5	8
160	Role of beryllium doping in strain changes in II-type InAs/GaSb superlattice investigated by high resolution X-ray diffraction method. <i>Applied Physics A: Materials Science and Processing</i> , <b>2012</b> , 108, 491-496	2.6	8
159	Structural and magnetic properties of nanoclusters in GaMnAs granular layers. <i>Journal of Solid State Chemistry</i> , <b>2011</b> , 184, 1530-1539	3.3	8
158	X-ray diffraction micro-imaging of strain in laterally overgrown GaAs layers. Part I: analysis of a single GaAs stripe. <i>Applied Physics A: Materials Science and Processing</i> , <b>2008</b> , 91, 601-607	2.6	8
157	ZnO crystals for substrates in micro and optoelectronic applications. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2006</b> , 3, 793-796		8
156	Crystallization of free standing bulk GaN by HVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2006</b> , 3, 1453-1456		8
155	CdSxTe1-x: bulk vapour growth, twin formation and the electrical activity of twin boundaries. <i>Journal Physics D: Applied Physics</i> , <b>2002</b> , 35, 1997-2007	3	8
154	Epitaxy of ternary nitrides on GaN single crystals. <i>Journal of Crystal Growth</i> , <b>1999</b> , 198-199, 1061-1065	1.6	8
153	Influence of high hydrostatic pressure/high temperature treatment on defect structure of AlGaAs layers. <i>Journal of Alloys and Compounds</i> , <b>1999</b> , 286, 279-283	5.7	8

152	Monocrystalline and Polycrystalline ZnO and ZnMnO Films Grown by Atomic Layer Epitaxy - Growth and Characterization. <i>Acta Physica Polonica A</i> , <b>2004</b> , 105, 667-673	0.6	8
151	Defect Structure of High-Temperature-Grown GaMnSb/GaSb. <i>Acta Physica Polonica A</i> , <b>2010</b> , 117, 341-343	0.6	8
150	Epitaxial ZnO Films Grown at Low Temperature for Novel Electronic Application. <i>Acta Physica Polonica A</i> , <b>2011</b> , 120, A-7-A-10	0.6	8
149	Technology of Ultrathin NbN and NbTiN Films for Superconducting Photodetectors. <i>Acta Physica Polonica A</i> , <b>2011</b> , 120, A-76-A-79	0.6	8
148	Defects and their Electronic Properties in High-Pressure-Annealed SOI Structures Sliced by Hydrogen <b>2002</b> , 269-288		8
147	Investigation of Cd $1-x$ Mg $x$ Te as possible materials for X and gamma ray detectors. <i>Journal of Crystal Growth</i> , <b>2018</b> , 491, 73-76	1.6	7
146	Photoconductive and electro-optic effects in (Cd,Mg)Te single crystals measured in an experiment-on-chip configuration. <i>Applied Physics Letters</i> , <b>2017</b> , 111, 011108	3.4	7
145	Arrangement of GaN nanowires on Si(001) substrates studied by X-ray diffraction: Importance of silicon nitride interlayer. <i>Applied Surface Science</i> , <b>2017</b> , 425, 1014-1019	6.7	7
144	Effect of processing on microstructure of Si:Mn. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2009</b> , 159-160, 99-102	3.1	7
143	Effect of AlN interlayers in the structure of GaN-on-Si grown by plasma-assisted MBE. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 2010-2015	1.6	7
142	(Cd,Mn)Te detectors for characterization of X-ray emissions generated during laser-driven fusion experiments. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>2010</b> , 624, 649-655	1.2	7
141	Conductance anomalies in strained quantum wires: the case of PbSe and PbTe. <i>Superlattices and Microstructures</i> , <b>1997</b> , 22, 51-55	2.8	7
140	X-ray study of silicon crystal structure changes due to implantation with fast nitrogen ions. <i>Journal of Alloys and Compounds</i> , <b>2001</b> , 328, 237-241	5.7	7
139	X-ray diffraction and Raman scattering study of near-surface structure perfection of GaAs single crystals after anisotropic etching. <i>Journal of Alloys and Compounds</i> , <b>1999</b> , 286, 289-296	5.7	7
138	Lattice constants and thermal expansion of Al $x$ Ga $1-x$ As:Te. <i>Journal of Applied Physics</i> , <b>1995</b> , 78, 6994-6998	2.5	7
137	Ultrathin NbN Films for Superconducting Single-Photon Detectors. <i>Acta Physica Polonica A</i> , <b>2011</b> , 120, 200-203	0.6	7
136	Effects of impurity band in heavily doped ZnO:HCl. <i>Physica B: Condensed Matter</i> , <b>2019</b> , 553, 174-181	2.8	7
135	Monolithic cyan $\lambda$ -violet InGaN/GaN LED array. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2017</b> , 214, 1600815	1.6	6



134	Suppression of extended defects propagation in a laser diodes structure grown on (20-21) GaN. <i>Semiconductor Science and Technology</i> , <b>2016</b> , 31, 035001	1.8	6
133	Homoepitaxial growth by halide vapor phase epitaxy of semi-polar GaN on ammonothermal seeds. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SC1030	1.4	6
132	Electronic- and band-structure evolution in low-doped (Ga,Mn)As. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 053710	2.5	6
131	Growth and Characterization of (Cd, Mn)Te. <i>IEEE Transactions on Nuclear Science</i> , <b>2013</b> , 60, 3805-3814	1.7	6
130	Ferromagnetism and the electronic band structure in (Ga,Mn)(Bi,As) epitaxial layers. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 072402	3.4	6
129	Characterization of the Nonpolar GaN Substrate Obtained by Multistep Regrowth by Hydride Vapor Phase Epitaxy. <i>Applied Physics Express</i> , <b>2012</b> , 5, 011001	2.4	6
128	Structural and magnetic properties of GaAs:(Mn,Ga)As granular layers. <i>Physica Status Solidi (B): Basic Research</i> , <b>2011</b> , 248, 1609-1614	1.3	6
127	Structural and magnetic properties of the molecular beam epitaxy grown MnSb layers on GaAs substrates. <i>Journal of Applied Physics</i> , <b>2009</b> , 106, 083524	2.5	6
126	X-ray characterization of catalytically grown ZnTe and ZnMgTe nanowires. <i>Radiation Physics and Chemistry</i> , <b>2009</b> , 78, S120-S124	2.5	6
125	X-ray diffraction studies of epitaxial laterally overgrown (ELOG) GaN layers on sapphire substrates. <i>Journal of Crystal Growth</i> , <b>2002</b> , 245, 37-49	1.6	6
124	High-pressure structural and optical properties of wurtzite-type Zn <sub>1-x</sub> Mg <sub>x</sub> Se. <i>Journal of Alloys and Compounds</i> , <b>2004</b> , 371, 168-171	5.7	6
123	The influence of the ion implantation temperature and the dose rate on smart-cut <sup>®</sup> in GaAs. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>2005</b> , 240, 142-145	1.2	6
122	Effect of High Temperature-Pressure on GaAs Layers Grown on Vicinal Si Substrates. <i>Crystal Research and Technology</i> , <b>2001</b> , 36, 997-1003	1.3	6
121	Characterization of Silicon-on-Insulator Structures by High-Resolution X-Ray Diffraction. <i>Journal of the Electrochemical Society</i> , <b>2002</b> , 149, G490	3.9	6
120	Effect of stress on interface transformation in thin semiconducting layers. <i>Thin Solid Films</i> , <b>2000</b> , 380, 117-119	2.2	6
119	Low-temperature thermal expansion of Mg <sub>3</sub> N <sub>2</sub> . <i>Journal of Alloys and Compounds</i> , <b>2001</b> , 328, 272-275	5.7	6
118	Strain in hydrogen and oxygen implanted silicon and SOI structures annealed at high pressure. <i>Journal of Alloys and Compounds</i> , <b>2001</b> , 328, 181-186	5.7	6
117	Strain relaxation of Al <sub>x</sub> Ga <sub>1-x</sub> N epitaxial layers on GaN and SiC substrates. <i>Journal of Alloys and Compounds</i> , <b>1999</b> , 286, 284-288	5.7	6



116	Mask-Induced Strain in GaAs Layers Grown by Liquid Phase Epitaxial Lateral Overgrowth. <i>Materials Research Society Symposia Proceedings</i> , <b>1999</b> , 570, 273		6
115	Magnetic Properties of Short Period InGaMnAs/InGaAs Superlattices. <i>Acta Physica Polonica A</i> , <b>2002</b> , 102, 687-694	0.6	6
114	Epitaxial Growth and Optical Properties of PbTe/CdTe Semiconductor Heterostructures. <i>Acta Physica Polonica A</i> , <b>2008</b> , 114, 1391-1396	0.6	6
113	Cubic MnTe - Growth by Molecular Beam Epitaxy and Basic Structural Characterization. <i>Acta Physica Polonica A</i> , <b>1995</b> , 87, 433-436	0.6	6
112	Transformation of AlGaAs/GaAs Interface under Hydrostatic Pressure. <i>Acta Physica Polonica A</i> , <b>1996</b> , 89, 405-409	0.6	6
111	The effect of transglutaminase on colloidal stability of milk proteins. <i>Journal of Food Measurement and Characterization</i> , <b>2019</b> , 13, 2339-2346	2.8	5
110	Structural defects and cathodoluminescence of In <sub>x</sub> Ga <sub>1-x</sub> N layers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 2248-2250		5
109	Creation of MnAs nanoclusters during processing of GaMnAs. <i>Radiation Physics and Chemistry</i> , <b>2009</b> , 78, S116-S119	2.5	5
108	Influence of a GaN Cap Layer on the Morphology and the Physical Properties of Embedded Self-Organized InN Quantum Dots on GaN(0001) Grown by MetalOrganic Vapour Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 031004	1.4	5
107	X-ray diffractometry and topography of lattice plane curvature in thermally deformed Si wafer. <i>Journal of Synchrotron Radiation</i> , <b>2008</b> , 15, 96-9	2.4	5
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105	Defect transformation study in silicon-on-insulator structures by high-resolution X-Ray diffraction. <i>Materials Science in Semiconductor Processing</i> , <b>2001</b> , 4, 35-37	4.3	5
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